

Silicon NPN Power Transistors

2SC3822

DESCRIPTION

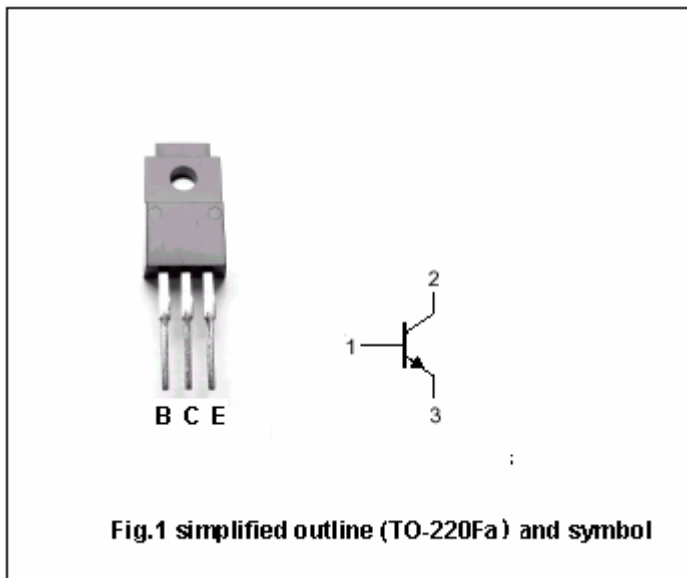
- With TO-220Fa package
- High voltage ,high speed

APPLICATIONS

- For power switching ,power amplifier, power driver and electronic supply applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	450	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
P_C	Collector dissipation	$T_C=25^\circ C$	30	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	400			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.4A			0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A ; I _B =0.4A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =450V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			1.0	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	10		30	
f _T	Transition frequency	I _C =0.1A ; V _{CE} =10V		100		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V		25		pF

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PACKAGE OUTLINE

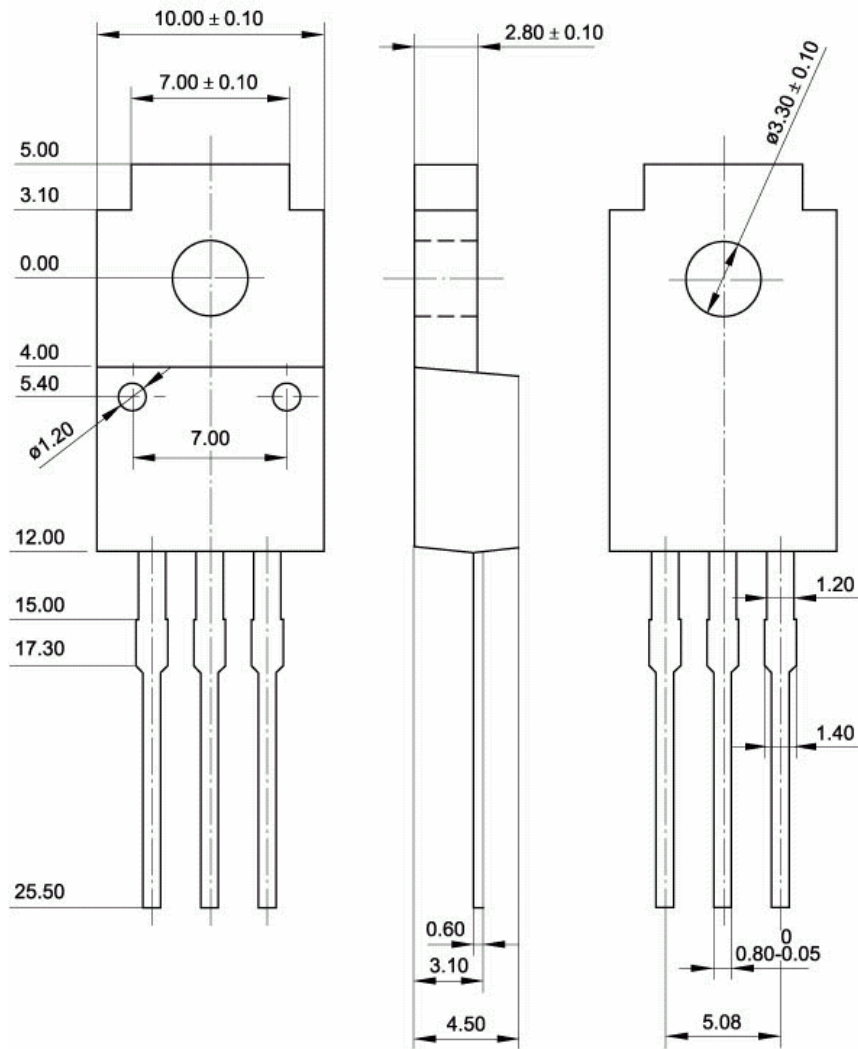


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)